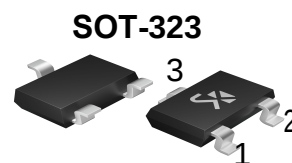


NPN Silicon Epitaxial Planar Transistor

FEATURES

- Complementary to MMBT5401W
- Small Surface Mount Package
- Ideal for Medium Power Amplification and Switching



1. BASE
2. EMITTER
3. COLLECTOR

MARKING:K4N

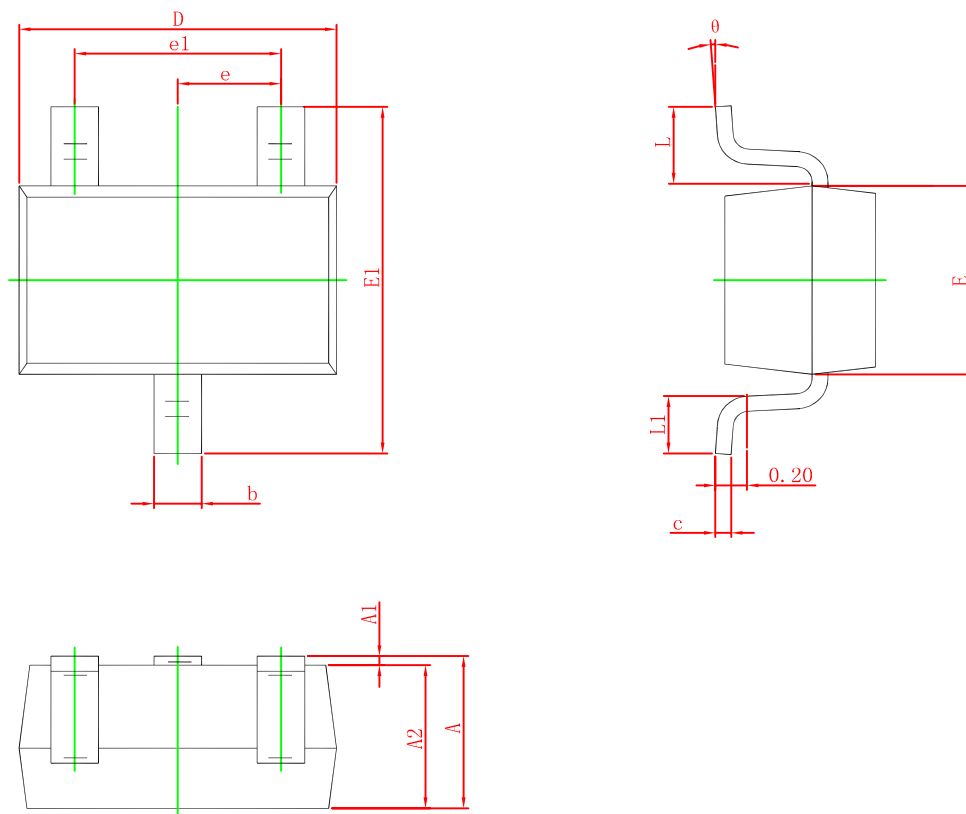
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Power Dissipation	200	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-+150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient Air	625	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=120\text{V}, I_E=0$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.05	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$ $V_{CE}=5\text{V}, I_C=10\text{mA}$ $V_{CE}=5\text{V}, I_C=50\text{mA}$	80 80 30		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$ $I_C=50\text{mA}, I_B=5\text{mA}$			0.15 0.2	V
Collector-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$ $I_C=50\text{mA}, I_B=5\text{mA}$			1 1	V
Output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			6	pF
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}$ $f=100\text{MHz}$	100		300	MHz

SOT-323 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°